

46 mΩ, Slew Rate Controlled Load Switch in uDFN4 1.1 mm x 1.1 mm

DESCRIPTION

The SiP32472 is a slew rate controlled integrated high side load switch that operates in the input voltage range from 1.2 V to 5.5 V.

This design features slew rate control, reverse blocking, output discharge, and control logic pull down. The device is logic high enabled.

The SiP32472 is available in uDFN4 1.1 mm x 1.1 mm package.

FEATURES

- Low input voltage, 1.2 V to 5.5 V
- Low R_{on} , 46 mΩ/typ. at 5 V
- Slew rate control
- Low logic control
- Reverse current blocking when disabled
- Integrated output discharge switch
- Integrated pull down resistor at “EN”
- uDFN4 1.1 mm x 1.1 mm package
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Smart phones
- GPS and portable media players
- Tablet computer
- Medical and healthcare equipment
- Industrial and instrument
- Game console

DEVICE OPTIONS

PART NUMBER	R_{on} (mΩ)	t_{on} (μs)	$t_{d(off)}$	REVERSE BLOCKING	$R_{DISCHARGE}$	EN _{LOGIC}	EN/PULL DOWN RESISTOR (Ω)
SiP32472DN-T1-GE3	46	200	2	Y	Y	High enable	2 M

TYPICAL APPLICATION CIRCUIT

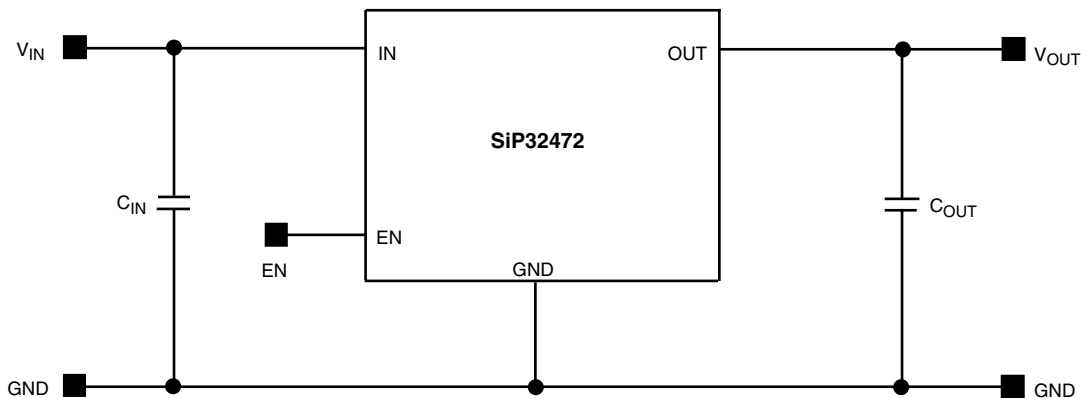


Fig. 1 - Typical Application Circuit



ABSOLUTE MAXIMUM RATINGS			
PARAMETER	CONDITIONS	LIMIT	UNIT
Supply Input Voltage V_{IN}	Reference to GND	- 0.3 to 6.5	V
Output Voltage V_{OUT}	Reference to GND	- 0.3 to 6.5	
Output Voltage V_{OUT}	Pulse at 1 ms reference to GND ⁽¹⁾	- 1.6	
Enable Input Voltage EN	Reference to GND	- 0.3 to 6.5	
Maximum Continuous Switch Current		1.2	A
Maximum Pulse Switch Current	Pulse at 1 ms, 10 % duty cycle	2	
ESD Rating (HBM)		4000	V
Thermal Resistance		280	°C/W
TEMPERATURE			
Operating Temperature		- 40 to 85	°C
Operating Junction Temperature		125	
Storage Temperature		- 65 to 150	

Note

⁽¹⁾ Negative current injection up to 300 mA

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING RANGE				
ELECTRICAL PARAMETER	MINIMUM	TYPICAL	MAXIMUM	UNIT
Input Voltage (V_{IN})	1.2	-	5.5	V

SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITION UNLESS SPECIFIED $V_{IN} = 1.2\text{ V to }5.5\text{ V}$, $T_A = -40\text{ °C to }85\text{ °C}$ (Typical values are at 25 °C)	LIMITS			UNIT
			MIN.	TYP.	MAX.	
POWER SUPPLY						
Quiescent Current	I_Q	$V_{IN} = 3.3\text{ V}$, $I_{OUT} = 0\text{ mA}$	-	4.5	7	μA
Shutdown Current	I_{SD}	OUT = GND	-	0.01	2	
Off Switch Current	$I_{DS(off)}$	EN = GND, OUT = GND	-	0.01	2	
Reverse Blocking Current	$I_{(in)RB}$	Out = 5 V, IN = 1.2 V, EN = 0 V, (Measured at IN pin)	-	0.01	1	
		Out = 5 V, IN = 0 V, EN = 0 V, (Measured at IN pin)	-	0.01	1	
SWITCH RESISTANCE						
On Resistance	$R_{DS(on)}$	$I_{OUT} = 500\text{ mA}$, $V_{IN} = 1.2\text{ V}$, $T_A = 25\text{ °C}$	-	86	130	mΩ
		$I_{OUT} = 500\text{ mA}$, $V_{IN} = 1.5\text{ V}$, $T_A = 25\text{ °C}$	-	72	100	
		$I_{OUT} = 500\text{ mA}$, $V_{IN} = 1.8\text{ V}$, $T_A = 25\text{ °C}$	-	62	90	
		$I_{OUT} = 500\text{ mA}$, $V_{IN} = 3\text{ V}$, $T_A = 25\text{ °C}$	-	48	60	
		$I_{OUT} = 500\text{ mA}$, $V_{IN} = 5\text{ V}$, $T_A = 25\text{ °C}$	-	46	60	
Discharge Switch On Resistance	R_{PD}	When $V_{IN} = 3\text{ V}$ at 25 °C	-	80	-	Ω
		When $V_{IN} = 1.8\text{ V}$ at 25 °C	-	< 200	-	
EN Pin Pull Down Resistor	R_{EN}	EN = 1.2 V	1	2.6	5	MΩ
On Resistance Temperature Coefficient	TC_{RDS}		-	2800		ppm/°C
ON/OFF LOGIC						
EN Input Low Voltage	V_{IL}	$V_{IN} = 1.5\text{ V}$	0.4	-	-	V
EN Input High Voltage	V_{IH}	$V_{IN} = 5.5\text{ V}$	-	-	1	

SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITION UNLESS SPECIFIED $V_{IN} = 1.2\text{ V to }5.5\text{ V}$, $T_A = -40\text{ }^\circ\text{C to }85\text{ }^\circ\text{C}$ (Typical values are at $25\text{ }^\circ\text{C}$)	LIMITS			UNIT
			MIN.	TYP.	MAX.	
SWITCHING SPEED						
Switch Turn-ON Delay Time	t_{on_DLY}	$R_{LOAD} = 500\ \Omega$, $C_L = 0.1\ \mu\text{F}$ $V_{IN} = 5\text{ V}$	-	130	-	μs
Switch Turn-ON Rise Time	t_r	$R_{LOAD} = 500\ \Omega$, $C_L = 0.1\ \mu\text{F}$ $V_{IN} = 5\text{ V}$	-	170	-	
Switch Turn-OFF Delay Time	t_{off}	$R_{LOAD} = 500\ \Omega$, $C_L = 0.1\ \mu\text{F}$, (50 % V_{IN} to 90 % V_{OUT})	-	2	-	

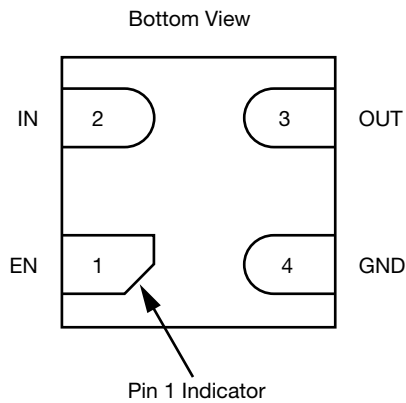
PIN CONFIGURATION


Fig. 2 - uDFN 1.1 mm x 1.1 mm Package

PIN DESCRIPTION (uDFN PACKAGE)		
PIN#	NAME	FUNCTION
1	EN	Switch on/off control. A pull down resistor is integrated
2	IN	Switch input
3	OUT	Switch output
4	GND	Ground connection

DEVICE MARKING		
Row 1	C + W	: W = week code
Row 2	Dot	: Dot is Pin 1 locator
SiP32472 = C		

TRUTH TABLE	
EN	SWITCH
1	ON
0	OFF

BLOCK DIAGRAM

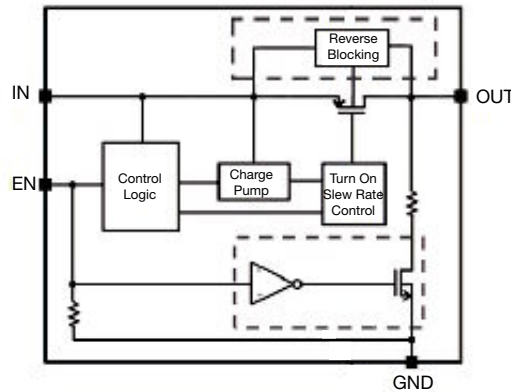


Fig. 3 - Functional Block Diagram

TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

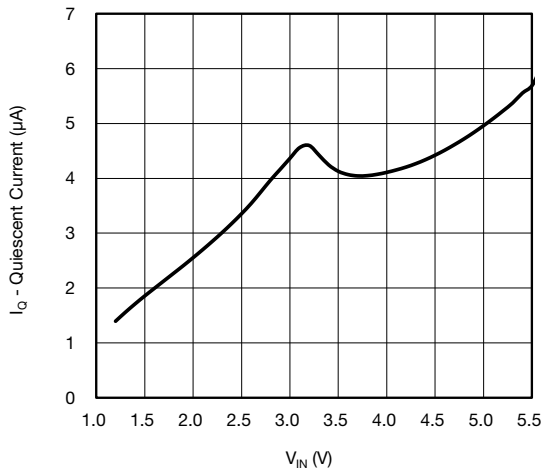


Fig. 4 - Quiescent Current vs. Input Voltage

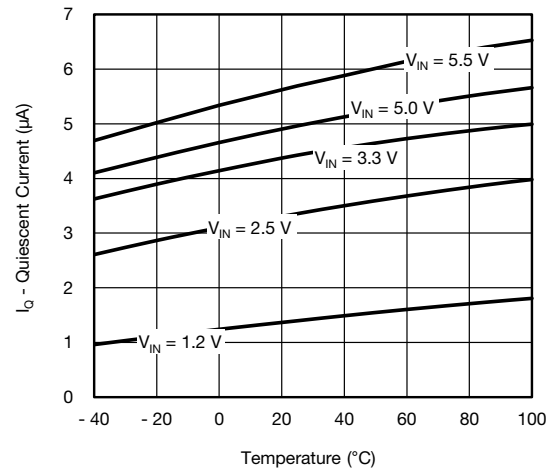


Fig. 6 - Quiescent Current vs. Temperature

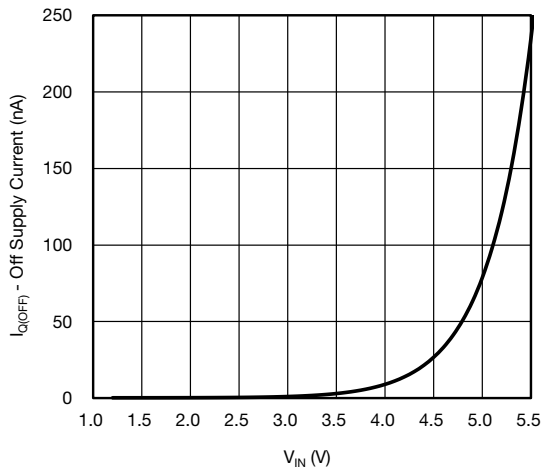


Fig. 5 - Off Supply Current vs. Input Voltage

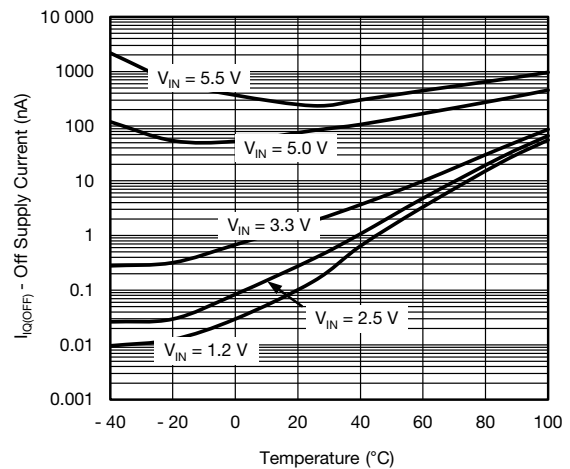


Fig. 7 - Off Supply Current vs. Temperature

TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

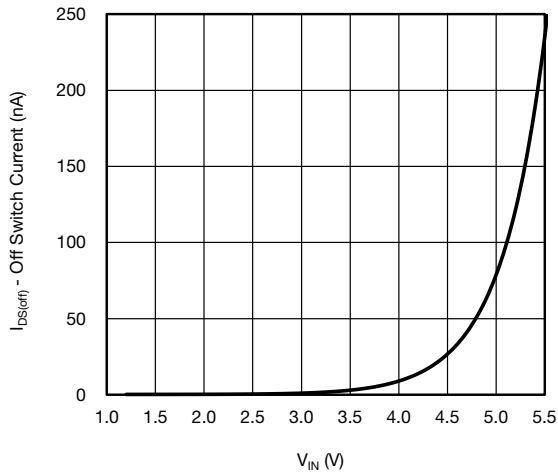


Fig. 8 - Off Switch Current vs. Input Voltage

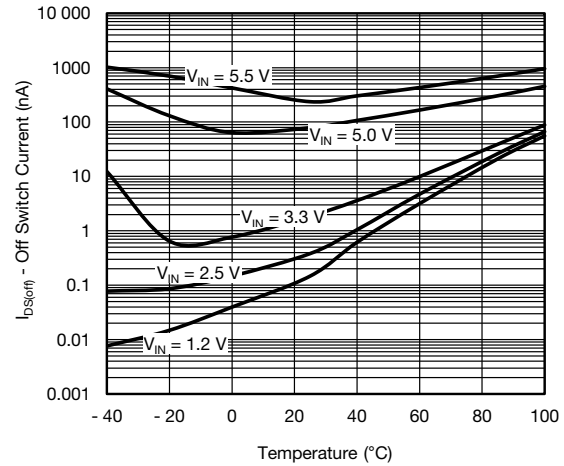


Fig. 11 - Off Switch Current vs. Temperature

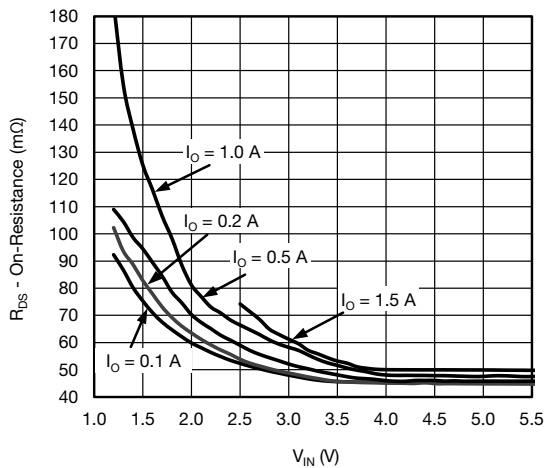


Fig. 9 - $R_{DS(on)}$ vs. Input Voltage

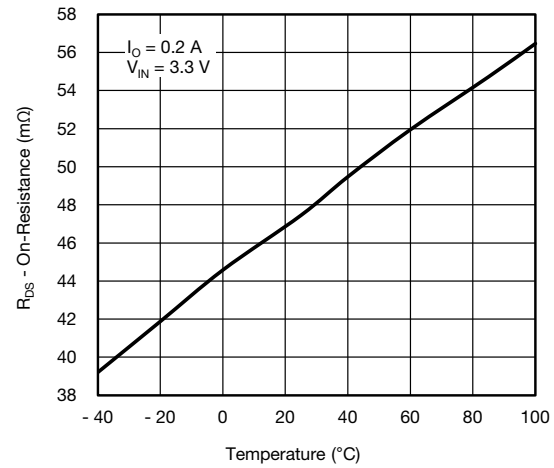


Fig. 12 - $R_{DS(on)}$ vs. Temperature

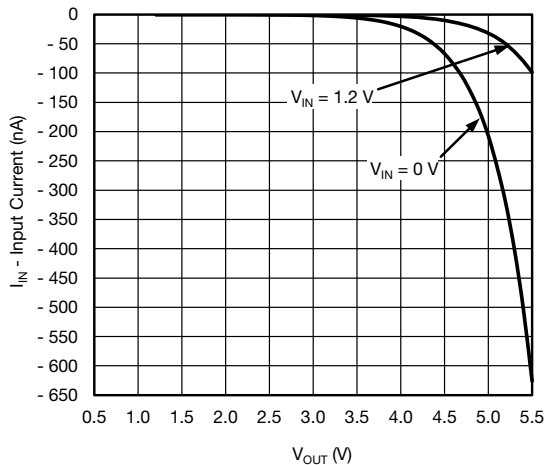


Fig. 10 - Reverse Blocking Current vs. Output Voltage

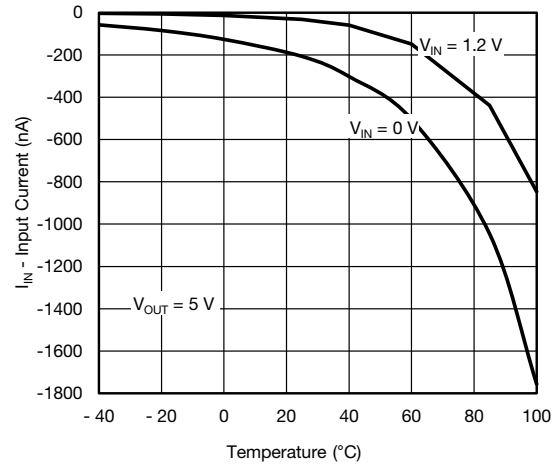


Fig. 13 - Reverse Blocking Current vs. Temperature

TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

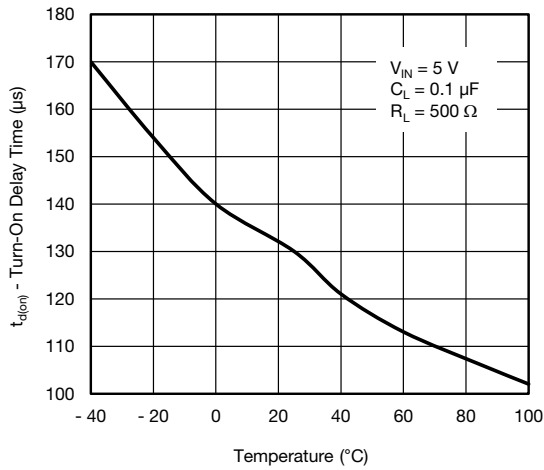


Fig. 14 - Turn-On Delay Time vs. Temperature

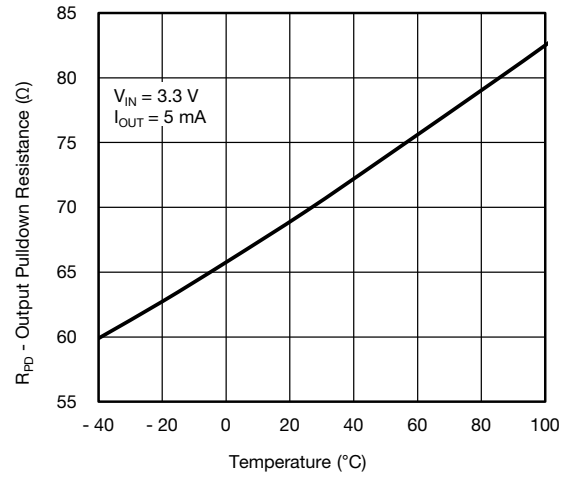


Fig. 17 - Output Pulldown Resistance vs. Temperature

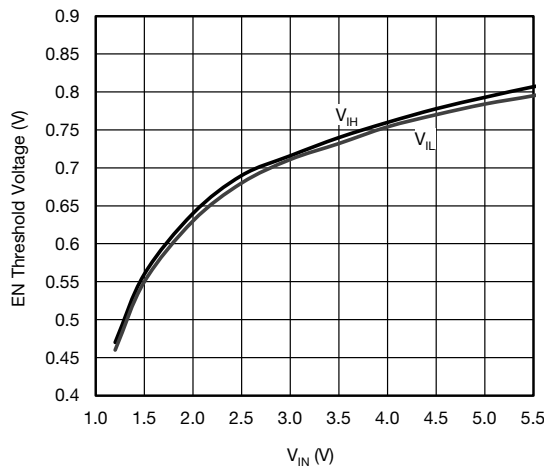


Fig. 15 - EN Threshold Voltage vs. Input Voltage

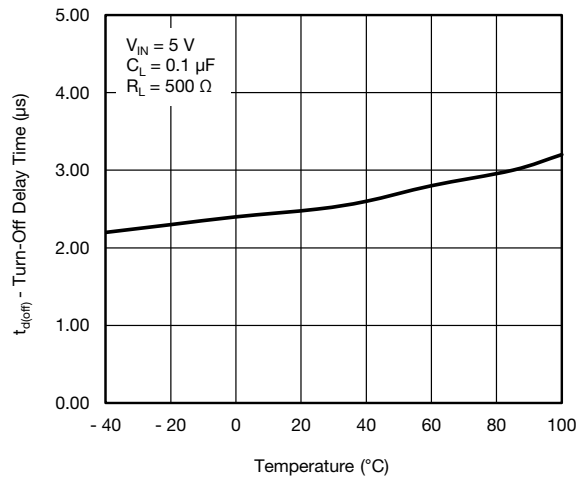


Fig. 18 - Turn-Off Delay Time vs. Temperature

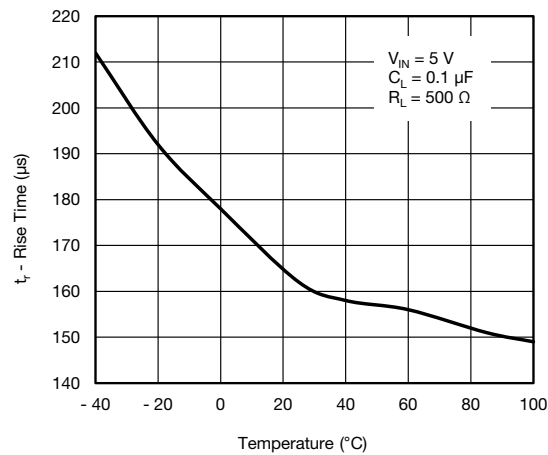


Fig. 16 - Rise Time vs. Temperature

TYPICAL WAVEFORMS

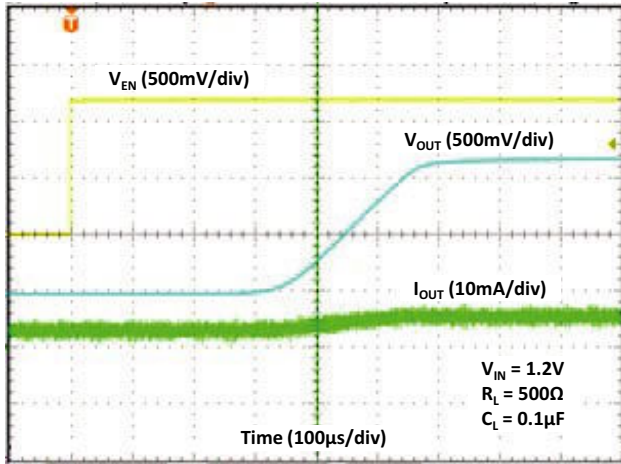


Fig. 19 - Turn-On Time

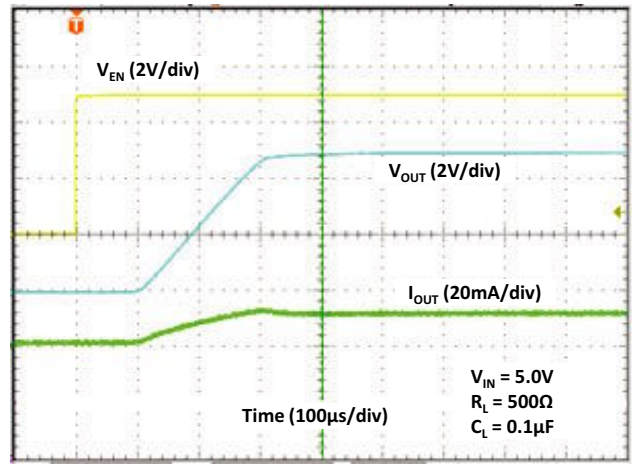


Fig. 22 - Turn-On Time

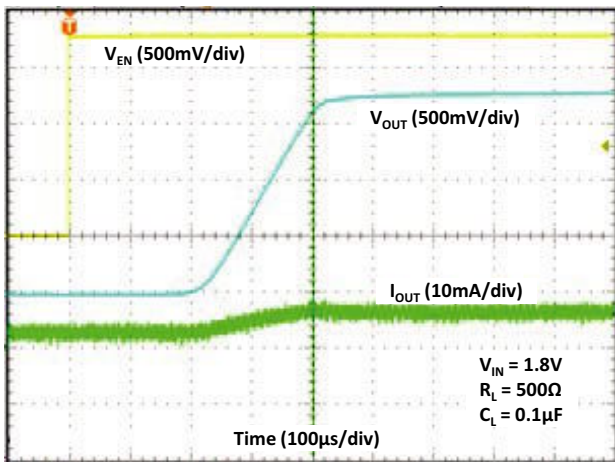


Fig. 20 - Turn-On Time

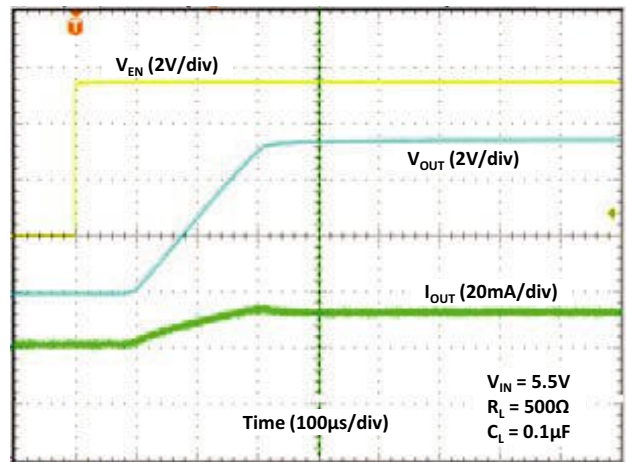


Fig. 23 - Turn-On Time

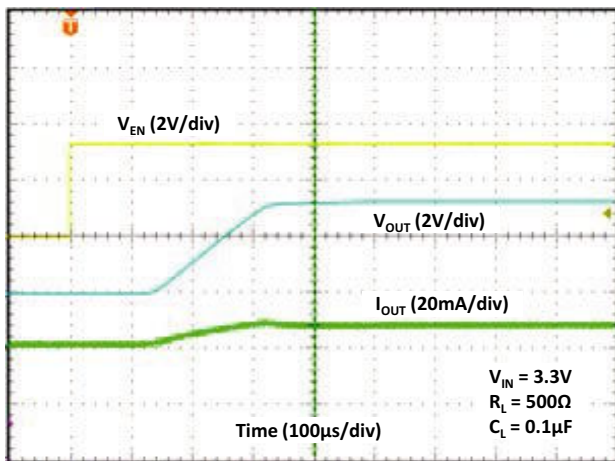


Fig. 21 - Turn-On Time

TYPICAL WAVEFORMS

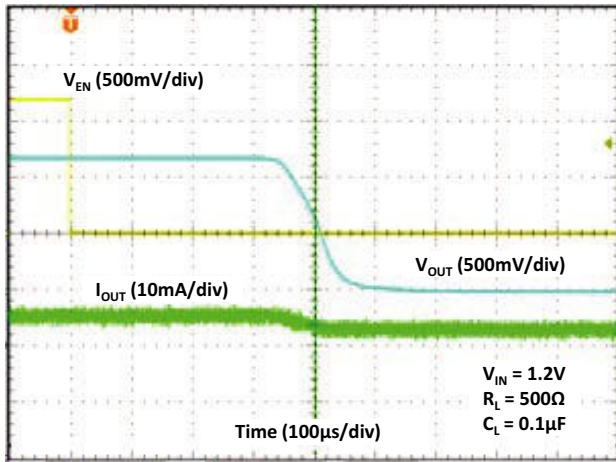


Fig. 24 - Turn-Off Time

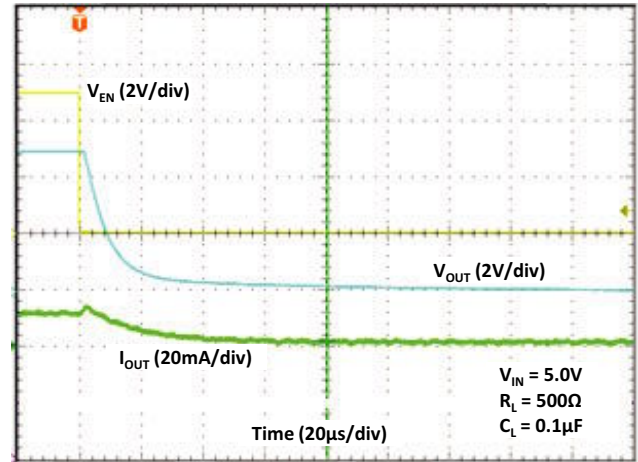


Fig. 27 - Turn-Off Time

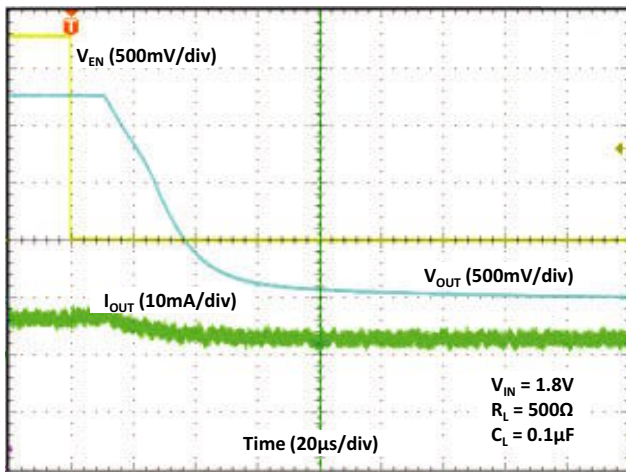


Fig. 25 - Turn-Off Time

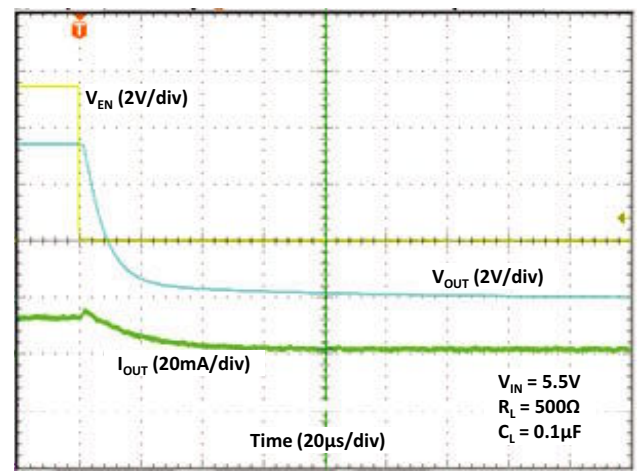


Fig. 28 - Turn-Off Time

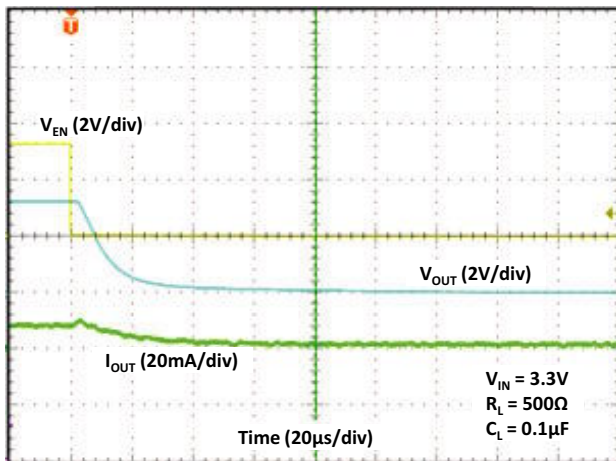


Fig. 26 - Turn-Off Time



DETAILED DESCRIPTION

SiP32472 has a P-channel power MOSFET designed as a high side load switch. It incorporates a negative charge pump at the gate to keep the gate to source voltage high when turned on therefore keep the on resistance low at lower input voltage range. SiP32472 is designed with slow slew rate to minimize the inrush current during turn on. This device has a reverse blocking circuit to prevent the current from going back to the input in case the output voltage is higher than the input voltage. The SiP32472 has an output pulldown resistor to discharge the output capacitance when the device is off.

APPLICATION INFORMATION

Input Capacitor

While a bypass capacitor on the input is not required, a 4.7 μF or larger capacitor for C_{IN} is recommended in almost all applications. The bypass capacitor should be placed as physically close as possible to the input pin to be effective in minimizing transients on the input. Ceramic capacitors are recommended over tantalum because of their ability to withstand input current surges from low impedance sources such as batteries in portable devices.

Output Capacitor

A 0.1 μF capacitor across V_{OUT} and GND is recommended to insure proper slew operation. There is inrush current through the output MOSFET and the magnitude of the inrush current depends on the output capacitor, the bigger the C_{OUT} the higher the inrush current. There are no ESR or capacitor type requirement.

Enable

The EN pin is compatible with CMOS logic voltage levels. It requires at least 0.4 V or below to fully shut down the device and 1 V or above to fully turn on the device. There is a 2.8 MΩ resistor connected between EN pin and GND pin.

Protection Against Reverse Voltage Condition

This device contains a reverse blocking circuit to keep the output current from flowing back to the input in case the output voltage is higher than the input voltage.

Thermal Considerations

This device is designed to maintain a constant output load current. Due to physical limitations of the layout and assembly of the device the maximum switch current is 1.2 A as stated in the Absolute Maximum Ratings table. However, another limiting characteristic for the safe operating load current is the thermal power dissipation of the package. To obtain the highest power dissipation (and a thermal resistance of 280 °C/W) the device should be connected to a heat sink on the printed circuit board.

The maximum power dissipation in any application is dependant on the maximum junction temperature, T_{J(max.)} = 125 °C, the junction-to-ambient thermal resistance, θ_{J-A} = 280 °C/W, and the ambient temperature, T_A, which may be formulaically expressed as:

$$P \text{ (max.)} = \frac{T_J \text{ (max.)} - T_A}{\theta_{J-A}} = \frac{125 - T_A}{280}$$

It then follows that, assuming an ambient temperature of 70 °C, the maximum power dissipation will be limited to about 196 mW.

So long as the load current is below the 1.2 A limit, the maximum continuous switch current becomes a function two things: the package power dissipation and the R_{DS(ON)} at the ambient temperature.

As an example let us calculate the worst case maximum load current at T_A = 70 °C. The worst case R_{DS(ON)} at 25 °C is 65 mΩ at V_{IN} = 1.5 V. The R_{DS(ON)} at 70 °C can be extrapolated from this data using the following formula:

$$R_{DS(ON)} \text{ (at } 70 \text{ }^\circ\text{C)} = R_{DS(ON)} \text{ (at } 25 \text{ }^\circ\text{C)} \times (1 + T_C \times \Delta T)$$

Where T_C is 2820 ppm/°C. Continuing with the calculation we have

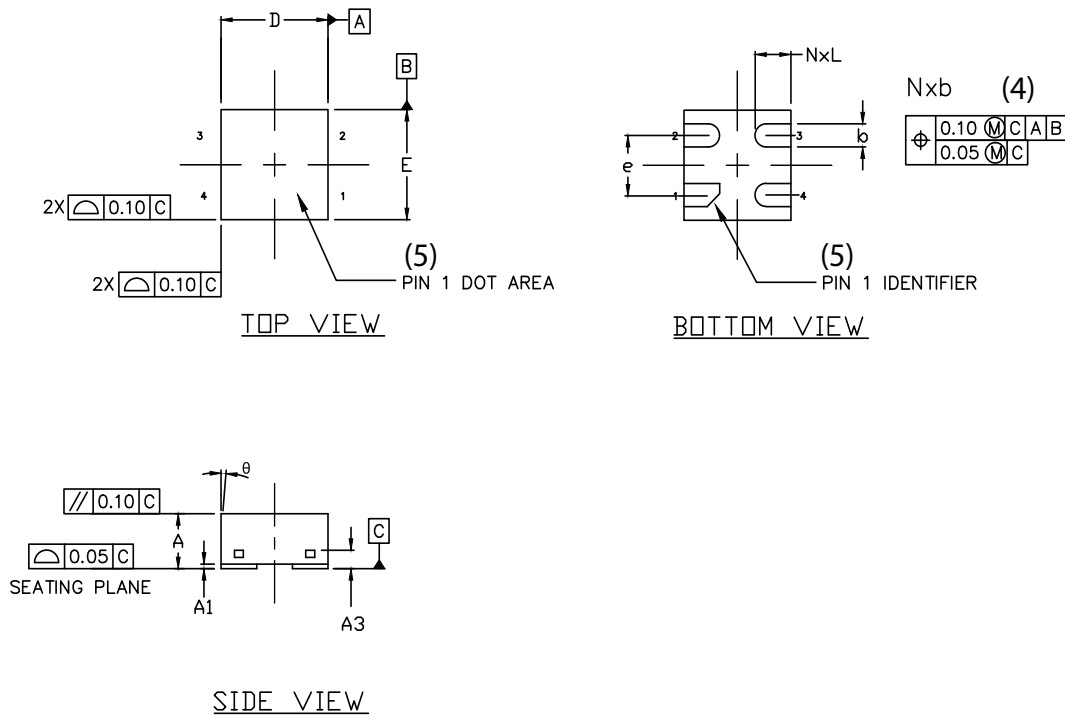
$$R_{DS(ON)} \text{ (at } 70 \text{ }^\circ\text{C)} = 65 \text{ m}\Omega \times (1 + 0.00282 \times (70 \text{ }^\circ\text{C} - 25 \text{ }^\circ\text{C})) = 73.2 \text{ m}\Omega$$

The maximum current limit is then determined by

$$I_{LOAD} \text{ (max.)} < \sqrt{\frac{P \text{ (max.)}}{R_{DS(ON)}}}$$

which in this case is 1.6 A. Under the stated input voltage condition, if the 1.6 A current limit is exceeded the internal die temperature will rise and eventually, possibly damage the device.

To avoid possible permanent damage to the device and keep a reasonable design margin, it is recommended to operate the device maximum up to 1.2 A only as listed in the Absolute Maximum Ratings table.

PACKAGE OUTLINE
uDFN4L - 1.1 mm x 1.1 mm Case Outline


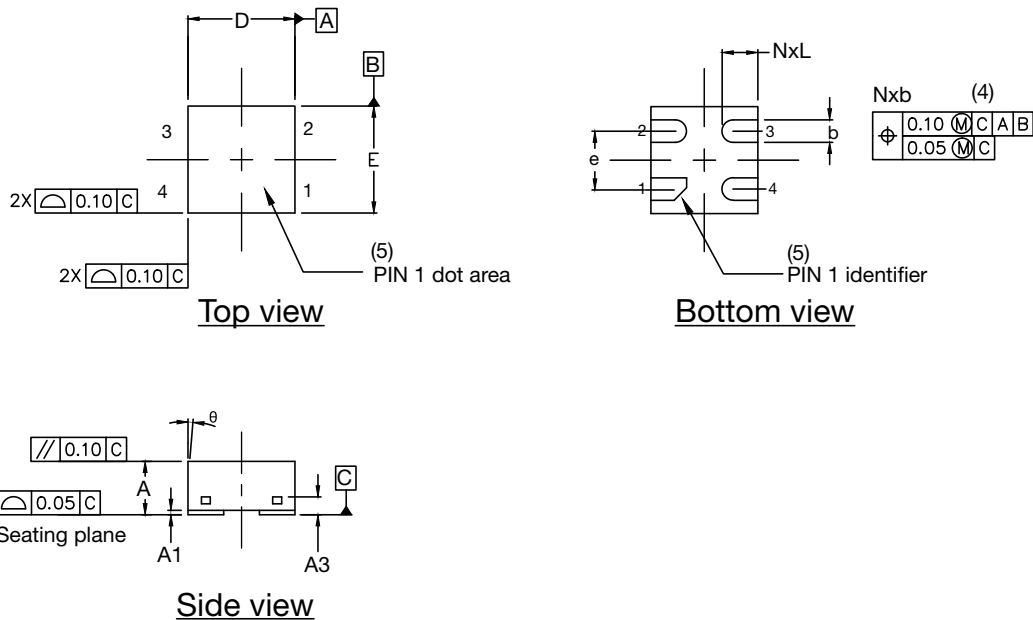
DIMENSION	MILLIMETERS ⁽¹⁾			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.50	0.55	0.60	0.020	0.022	0.024
A1	0	-	0.05	0	-	0.002
A3	0.15 REF			0.006 REF		
b	0.18	0.25	0.30	0.007	0.010	0.012
D	1.10 BSC			0.043 BSC		
e	0.65 BSC			0.026 BSC		
E	1.10 BSC			0.043 BSC		
L	0.30	0.40	0.50	0.012	0.016	0.020
θ	0°	-	12°	0°	-	12°
N ⁽³⁾	4			4		
Ne ⁽³⁾	2			2		

Notes

- (1) Use millimeters as the primary measurement.
- (2) Dimensioning and tolerances conform to ASME Y14.5M. - 1994.
- (3) N is the number of terminals. Ne is the number of terminals in E site.
- (4) Dimensions b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip.
- (5) The pin 1 identifier must be existed on the top surface of the package by using identification mark or other feature of package body.
- (6) Package warpage max. 0.05 mm.

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uDFN4L - 1.1 mm x 1.1 mm Case Outline



DIMENSION	MILLIMETERS ⁽¹⁾			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.50	0.55	0.60	0.020	0.022	0.024
A1	0	-	0.05	0	-	0.002
A3	0.15 REF			0.006 REF		
b	0.18	0.25	0.30	0.007	0.010	0.012
D	1.10 BSC			0.043 BSC		
e	0.65 BSC			0.026 BSC		
E	1.10 BSC			0.043 BSC		
L	0.30	0.40	0.50	0.012	0.016	0.020
θ	0°	-	12°	0°	-	12°
N ⁽³⁾	4			4		
Ne ⁽³⁾	2			2		

Notes

- (1) Use millimeters as the primary measurement.
- (2) Dimensioning and tolerances conform to ASME Y14.5M. - 1994.
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ECN: S13-1370-Rev. A, 24-Jun-13
DWG: 6015

RECOMMENDED MINIMUM PADS FOR TDFN4 1.2 x 1.6



Recommended Minimum Pads
Dimensions in mm



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